

/ Descriptions

TO-251	NPN	Silicon NPN transistor in a TO-251 Plastic Package.
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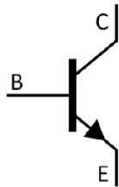
/ Features

Low collector-emitter saturation voltage, complementary to KTA1042I.

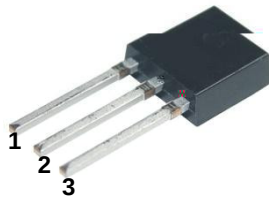
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1	Base	PIN 2	Collector	PIN 3	Emitter
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/ h_{FE} Classifications & Marking

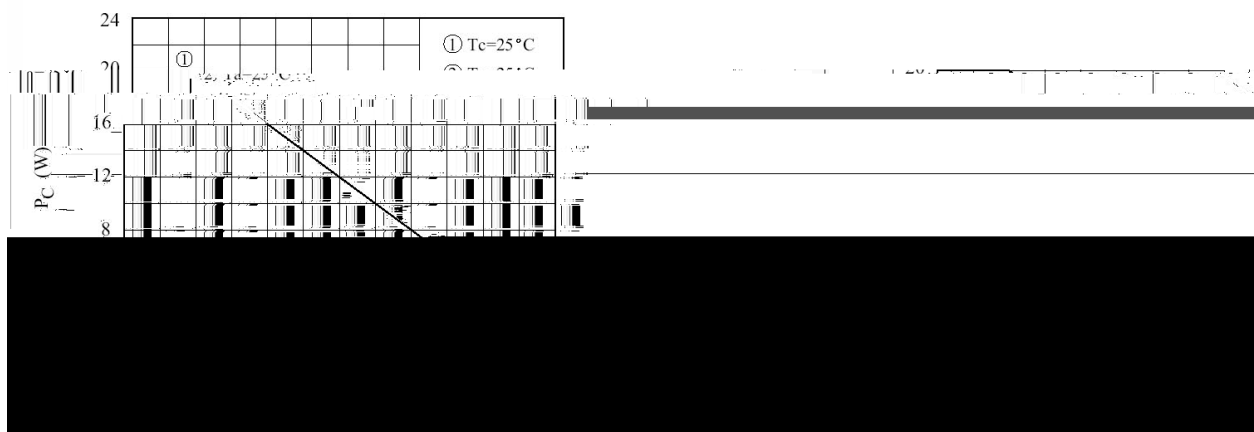
h _{FE} Classifications Symbol	O	Y
h _{FE} Range	70 140	120 240

/ Absolute Maximum Ratings(Ta=25)

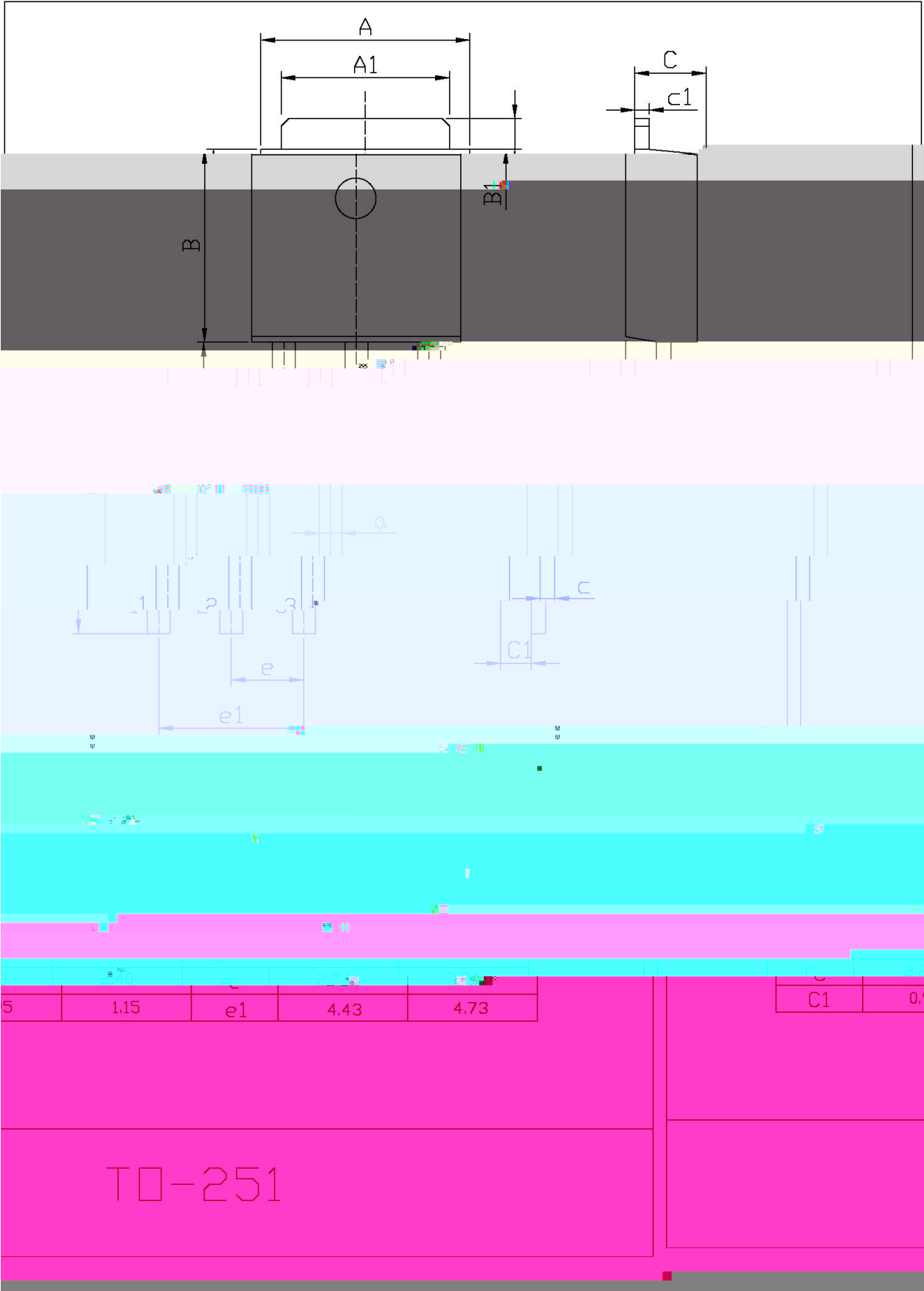
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	5	A
Base Current - Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

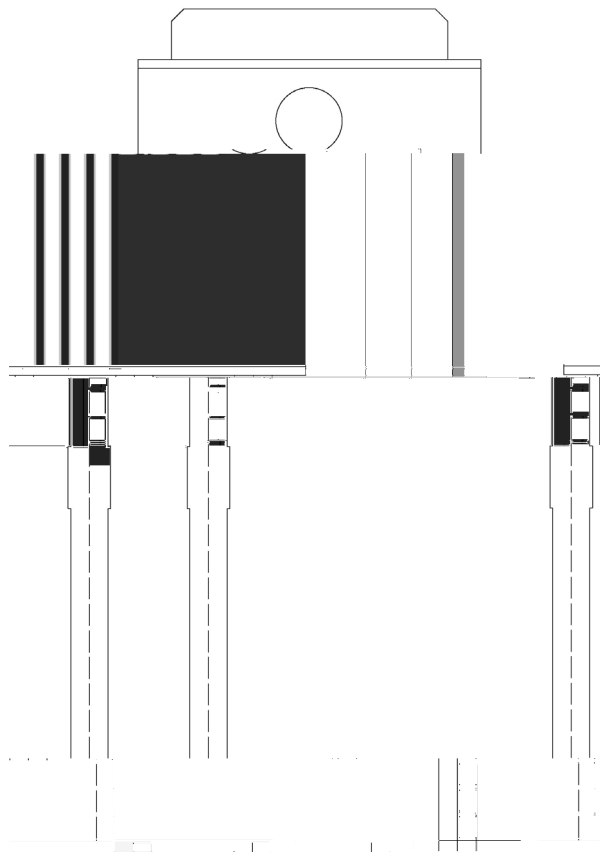
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=50mA$ $I_B=0$	100			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=100V$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5V$ $I_C=0$			1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V$ $I_C=1A$	70		240	
	$h_{FE(2)}$	$V_{CE}=5V$ $I_C=4A$	20			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A$ $I_B=0.4A$			2	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5V$ $I_C=1A$			1.5	V
Transition Frequency	f_T	$V_{CE}=5V$ $I_C=1A$		30		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1MHz$		40		pF



/ Package Dimensions



/ Marking Instructions



BR

C2022I

Y: h_{FE}

Note:

BR: Company Code

C2022I: Product Type.

Y: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

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